

MA3X200F

Silicon epitaxial planar type

For switching circuits

■ Features

- Two elements contained in one package, allowing high-density mounting
- Soft recovery characteristic (T_{rr} : 100 ns)
- Small terminal capacitance, C_t

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Reverse voltage (DC)	V_R	80	V	
Peak reverse voltage	V_{RM}	80	V	
Forward voltage (DC)	Single	I_F	100	mA
	Series		75	
Peak forward current	Single	I_{FM}	225	mA
	Series		170	
Non-repetitive peak forward surge current*	Single	I_{FSM}	500	mA
	Series		325	
Junction temperature	T_j	150	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$	

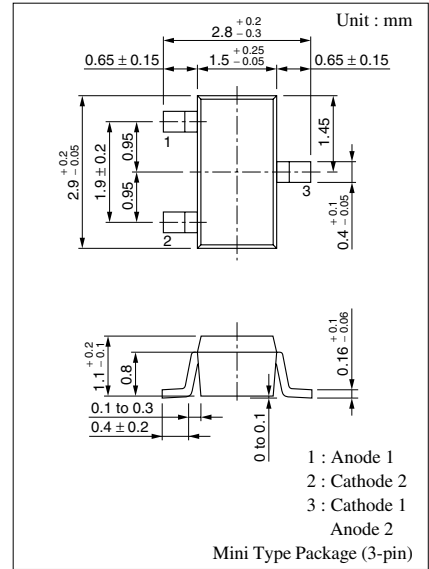
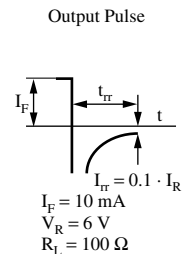
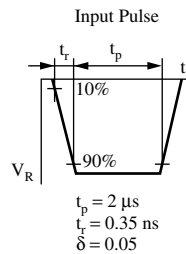
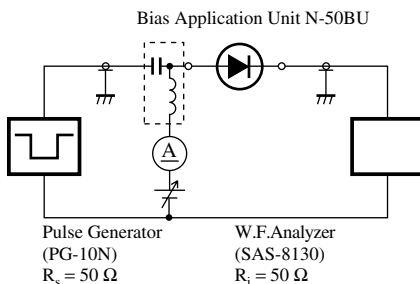
Note) * : $t = 1 \text{ s}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_{R1}	$V_R = 75 \text{ V}$			10	nA
	I_{R2}	$V_R = 5 \text{ V}, T_a = 85^\circ\text{C}$			20	nA
Forward voltage (DC)	V_F	$I_F = 100 \text{ mA}$			1.2	V
Reverse voltage (DC)	V_R	$I_R = 100 \mu\text{A}$	80			V
Terminal capacitance	C_t	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			2.5	pF
Reverse recovery time*	t_{rr}	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}$ $I_{rr} = 0.1 \cdot I_R, R_L = 100 \Omega$			100	ns

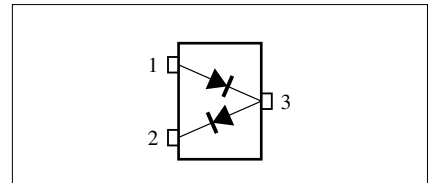
Note) 1. Rated input/output frequency: 100 MHz

2. * : t_{rr} measuring circuit

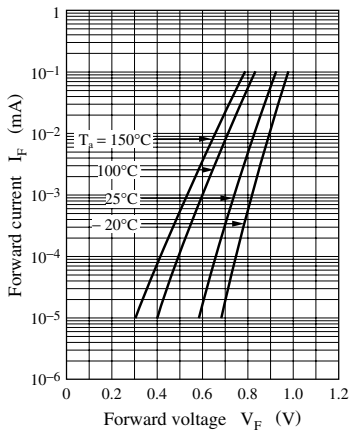


Marking Symbol: M5M

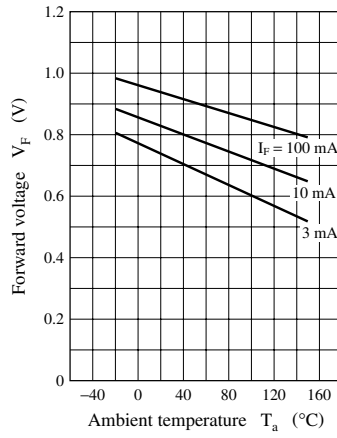
Internal Connection



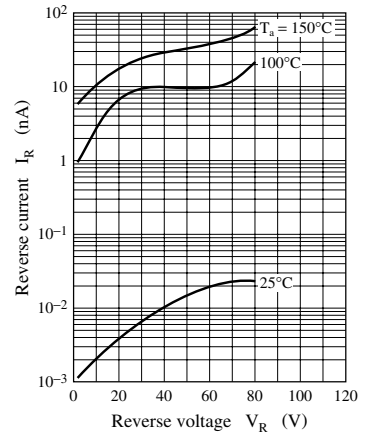
$I_F - V_F$



$V_F - T_a$



$I_R - V_R$



$I_R - T_a$

